

IGBT Chip in NPT-technology

**FEATURES:**

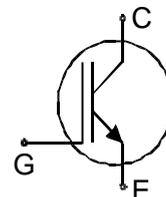
- 600V NPT technology
- 100µm chip
- short circuit prove
- positive temperature coefficient
- easy paralleling

**This chip is used for:**

- SGP20N60

**Applications:**

- drives



Chip Type	V <sub>CE</sub>	I <sub>Cn</sub>	Die Size	Package	Ordering Code
SIGC18T60SNC	600V	20A	4.3 x 4.3 mm <sup>2</sup>	sawn on foil	Q67041-S2856-A001
SIGC18T60SNC	600V	20A	4.3 x 4.3 mm <sup>2</sup>	unsawn	Q67041-S2856-A002

**MECHANICAL PARAMETER:**

Raster size	4.3 x 4.3	mm <sup>2</sup>
Area total / active	18.49 / 14.3	
Emitter pad size	2.48 x 2.98	
Gate pad size	0.7 x 1.08	
Thickness	100	µm
Wafer size	150	mm
Flat position	270	deg
Max.possible chips per wafer	796	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, ≤500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

## MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25\text{ °C}$	$V_{CE}$	600	V
DC collector current, limited by $T_{jmax}$	$I_C$	<sup>1)</sup>	A
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	60	A
Gate emitter voltage	$V_{GE}$	$\pm 20$	V
Operating junction and storage temperature	$T_j, T_{stg}$	-55 ... +150	$^{\circ}\text{C}$

<sup>1)</sup> depending on thermal properties of assembly

## STATIC CHARACTERISTICS (tested on chip), $T_j=25\text{ °C}$ , unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	600			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=20A$	1.6	1.9	2.5	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=500\mu A, V_{GE}=V_{CE}$	3	4	5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$			1.5	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$			120	nA

## DYNAMIC CHARACTERISTICS (tested at component):

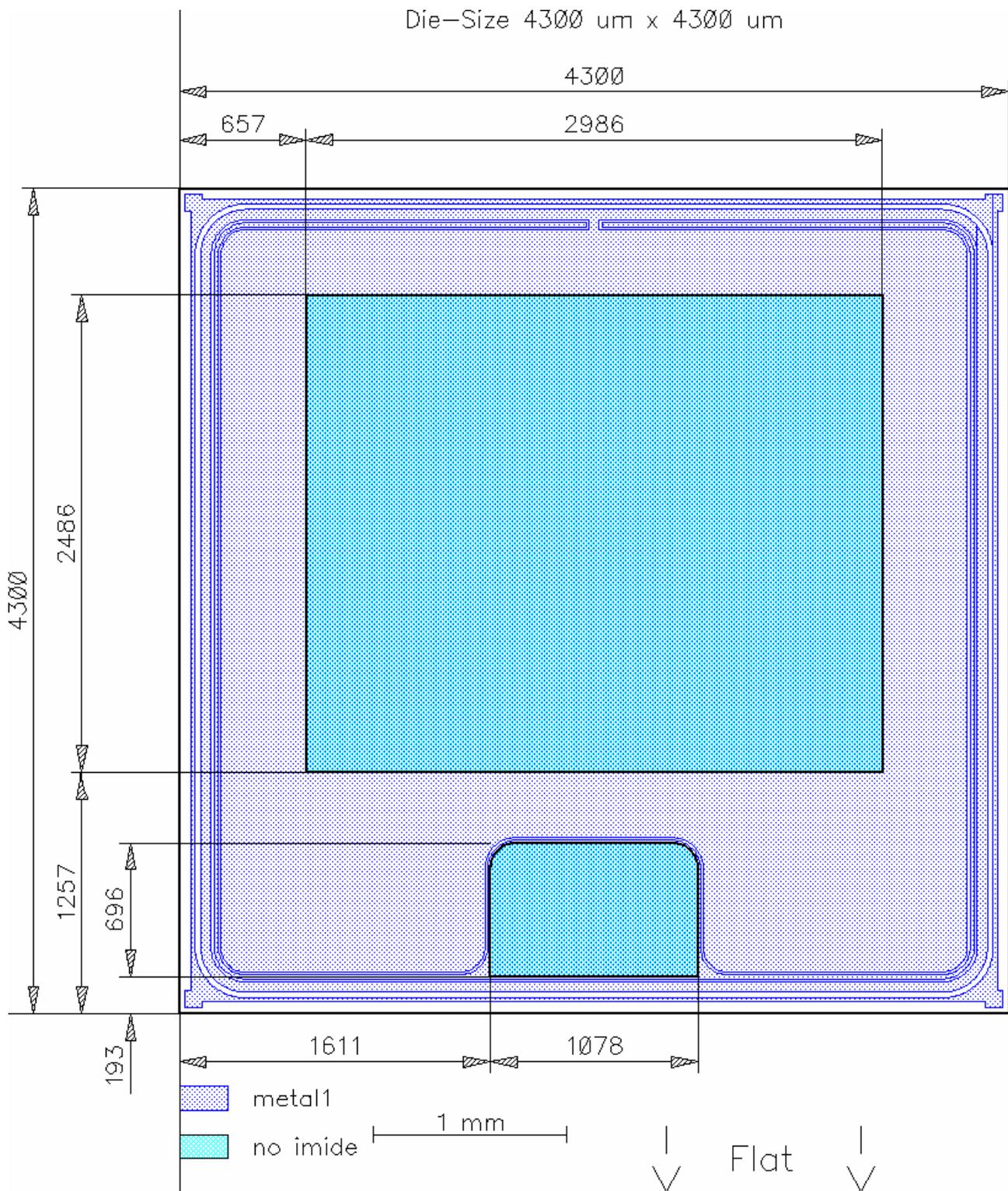
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25V$	-	1100	1320	pF
Output capacitance	$C_{oss}$	$V_{GE}=0V$	-	107	128	
Reverse transfer capacitance	$C_{riss}$	$f=1MHz$	-	63	75	

## SWITCHING CHARACTERISTICS (tested at component), Inductive Load:

Parameter	Symbol	Conditions <sup>2)</sup>	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=150\text{ °C}$	-	36	46	ns
Rise time	$t_r$	$V_{CC}=400V$	-	30	36	
Turn-off delay time	$t_{d(off)}$	$I_C=20A$	-	250	300	
Fall time	$t_f$	$V_{GE}=+15/0V$	-	63	76	
		$R_G=16\Omega$				

<sup>2)</sup> switching conditions different to 600V Standard IGBT 2, under comparable switching conditions 40% faster turnoff than Standard IGBT 2. Values also influenced by parasitic L- and C- in measurement and package.

**CHIP DRAWING:**





# SIGC18T60SNC

---

**FURTHER ELECTRICAL CHARACTERISTICS:**

---

This chip data sheet refers to the device data sheet

SGP20N60

Package :TO220

---

**Description:**

---

AQL 0,65 for visual inspection according to failure catalog

---

Electrostatic Discharge Sensitive Device according to MIL-STD 883

---

Test-Normen Villach/Prüffeld

---

**Published by**  
**Infineon Technologies AG,**  
**Bereich Kommunikation**  
**St.-Martin-Strasse 53,**  
**D-81541 München**  
**© Infineon Technologies AG 2002**  
**All Rights Reserved.**

**Attention please!**

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

**Information**

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives world-wide (see address list).

**Warnings**

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and / or maintain and sustain and / or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.